



# High Voltage NPN Transistor



#### TO-220



#### Pin Definition:

- 1. Base
- 2. Collector
- 3. Emitter

#### **PRODUCT SUMMARY**

BV <sub>CEO</sub>	420V
BV <sub>CBO</sub>	1050V
Ic	4A
V <sub>CE(SAT)</sub>	0.5V @ I <sub>C</sub> =1A, I <sub>B</sub> =0.2A

#### **Features**

- High Voltage Capability
- High Switching Speed

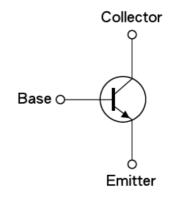
### **Structure**

- Silicon Triple Diffused Type
- NPN Silicon Transistor

## **Ordering Information**

Part No.	Package	Packing
TSC742CZ C0	TO-220	50pcs / Tube

#### **Block Diagram**



**Absolute Maximum Rating** (T<sub>A</sub> = 25°C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	$V_{CBO}$	1050	V
Collector-Emitter Voltage @ V <sub>BE</sub> =0V	$V_{CES}$	420	V
Emitter-Base Voltage	$V_{EBO}$	15	V
Collector Current	I <sub>C</sub>	4	А
Collector Peak Current (tp <5ms)	I <sub>CM</sub>	8	Α
Base Current	I <sub>B</sub>	2	Α
Base Peak Current (tp <5ms)	I <sub>BM</sub>	4	А
Power Total Dissipation @ Tc=25°C	P <sub>DTOT</sub>	70	W
Maximum Operating Junction Temperature	TJ	+150	°C
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	°C

**Note:** Single Pulse. P<sub>W</sub> = 300uS, Duty ≤2%

#### **Thermal Performance**

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	R⊖ <sub>JC</sub>	1.8	°C/W
Thermal Resistance - Junction to Ambient	R⊖ <sub>JA</sub>	62.5	°C/W

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**Electrical Specifications** (T<sub>A</sub> = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Collector-Base Voltage	I <sub>C</sub> =0.5mA	BV <sub>CBO</sub>	1050			V
Collector-Emitter Breakdown Voltage	I <sub>C</sub> =5mA	BV <sub>CEO</sub>	420			V
Emitter-Base Breakdown Voltage	I <sub>E</sub> =1mA	BV <sub>EBO</sub>	15			V
Collector Cutoff Current	$V_{CE} = 400V, I_{B} = 0$	I <sub>CEO</sub>		10	250	uA
Collector Cutoff Current	$V_{CB} = 950V, I_{E} = 0$	I <sub>CBO</sub>			10	uA
Collector-Emitter Saturation Voltage	I <sub>C</sub> =1A, I <sub>B</sub> =0.2A	V <sub>CE(SAT)</sub> 1		0.15	0.5	V
Collector-Emitter Saturation Voltage	I <sub>C</sub> =3.5A, I <sub>B</sub> =1A	V <sub>CE(SAT)</sub> 2		1.2	1.5	V
Base-Emitter Saturation Voltage	I <sub>C</sub> =3.5A, I <sub>B</sub> =1A	V <sub>BE(SAT)</sub> 1		1.0	1.5	V
DC Current Gain	$V_{CE} = 5V, I_{C} = 0.1A$	h <sub>FE</sub>	48	70	100	
	$V_{CE} = 3V, I_{C} = 0.8A$		23	28	50	
Resistive Load Switching Time (Ratings)						
Rise Time	\/ 5\/ L 0.5A	t <sub>r</sub>			1	uS
Storage Time	$V_{CC} = 5V, I_C = 0.5A,$ $t_P = 300uS,$	t <sub>STG</sub>	4.5	5	5.5	uS
Fall Time		t <sub>f</sub>			1.2	uS

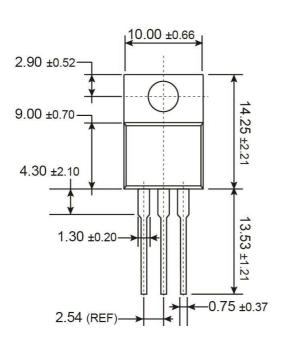
Notes: Pulsed duration =380uS, duty cycle ≤2%

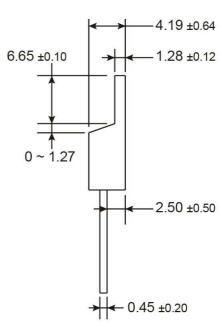
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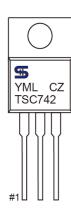
## **TO-220 Mechanical Drawing**





Unit: Millimeters

## **Marking Diagram**



Y = Year Code
 M = Month Code

 (A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug, I=Sep, J=Oct, K=Nov, L=Dec)

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L = Lot Code

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